

## Description

The PSM8PN03R4 uses split gate trench technology to provide excellent  $R_{DS(on)}$  low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

### MOSFET Product Summary

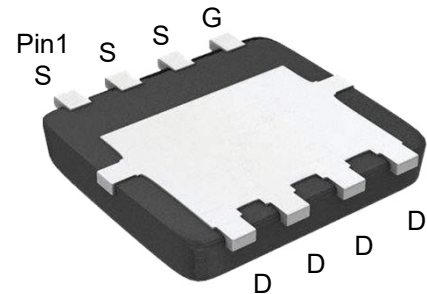
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
30	4.3@ $V_{GS} = 10V$	69
	7.0@ $V_{GS} = 4.5V$	

## Feature

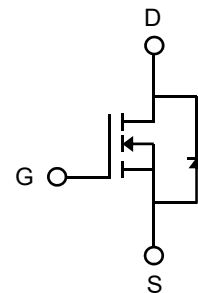
- Low  $R_{DS(on)}$  - Ensures On-State Losses are Minimized
- Excellent  $Q_{gd} \times R_{DS(on)}$  Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package  
Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

## Applications

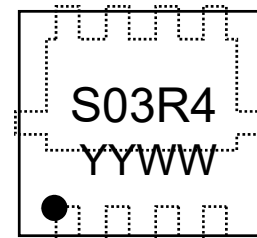
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



**Bottom View**



**Circuit Diagram**



Pin1

**Marking (Top View)**

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous <sup>1)</sup>	$I_D$	$T_C=25^\circ C$	69
		$T_C=100^\circ C$	44
Pulsed Drain Current <sup>2)</sup>	$I_{DM}$	280	A
Total Power Dissipation	$P_D$	37.8	W
Avalanche Current <sup>3)</sup>	$I_{AS}$	38	A
Avalanche Energy <sup>3)</sup>	$E_{AS}$	72.5	mJ
Thermal Resistance , Junction-case <sup>4)</sup>	$R_{\theta JC}$	3.29	$^\circ C/W$
Thermal Resistance Junction-to-Ambient <sup>5)</sup>	$R_{\theta JA}$	50.6	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

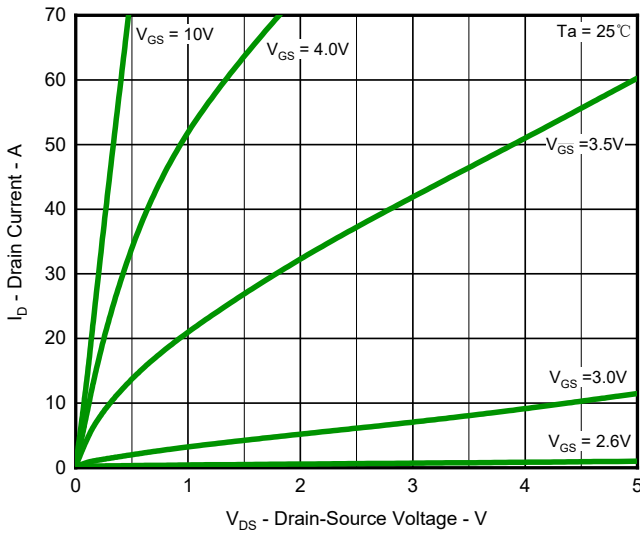
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	2.0	3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$	-	4.3	5.3	m $\Omega$
		$V_{GS} = 4.5V, I_D = 5A$	-	7.0	8.0	
<b>Dynamic Characteristics<sup>6)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	966	-	pF
Output Capacitance	$C_{oss}$		-	270	-	
Reverse Transfer Capacitance	$C_{rss}$		-	31	-	
<b>Switching Characteristics<sup>6)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{dd} = 15V, V_{GEN} = 10V,$ $I_D = 20A, R_{GEN} = 10\Omega$	-	4.3	-	ns
Turn-on Rise Time	$t_r$		-	5.3	-	
Turn-Off Delay Time	$t_{d(off)}$		-	26.1	-	
Turn-Off Fall Time	$t_f$		-	14.6	-	
Total Gate Charge	$Q_g$	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 20A$	-	14.6	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.0	-	
Gate-Drain Charge	$Q_{gd}$		-	1.3	-	
Gate Resistance	$R_g$	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	4.3	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 50A$	-	0.9	1.4	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F=10A, d_i/d_t=100A/\mu s$	-	12.5	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	3.6	-	nC

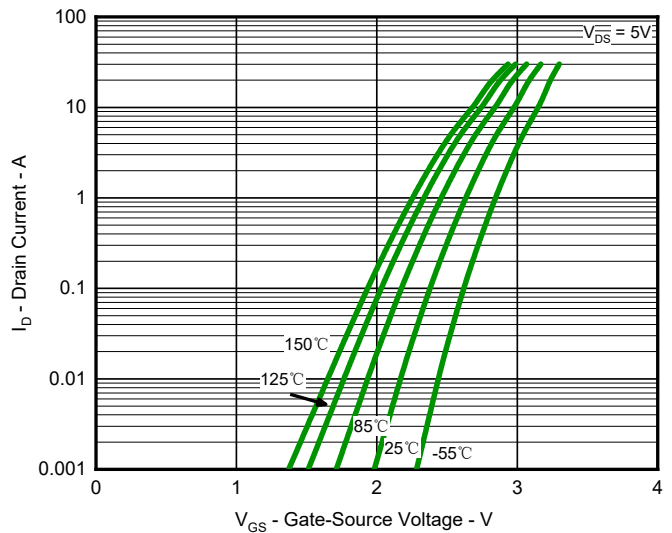
## Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=150^\circ C$ ).
3. This single-pulse measurement was taken under the following condition [ $L=100\mu H, V_{GS}=10V, V_{DS}=15V$ ]while it's value is limited by  $T_{J\_Max}=150^\circ C$ .
4. Device mounted on infinite heatsink.
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
6. Guaranteed by design, not subject to production.

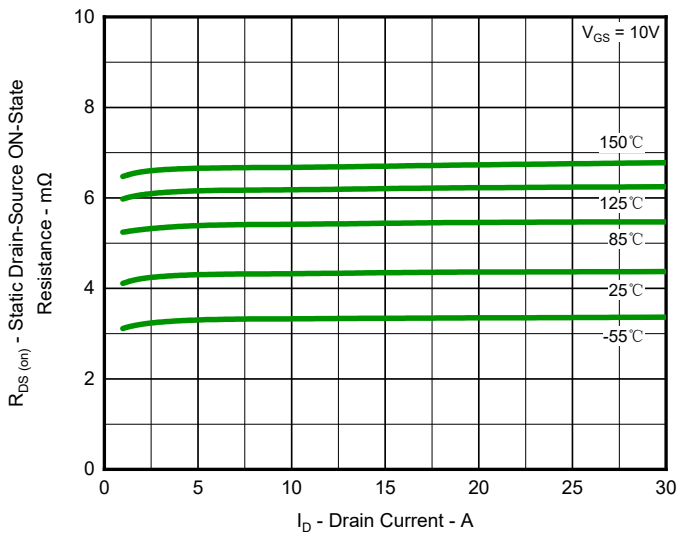
## Typical Characteristics



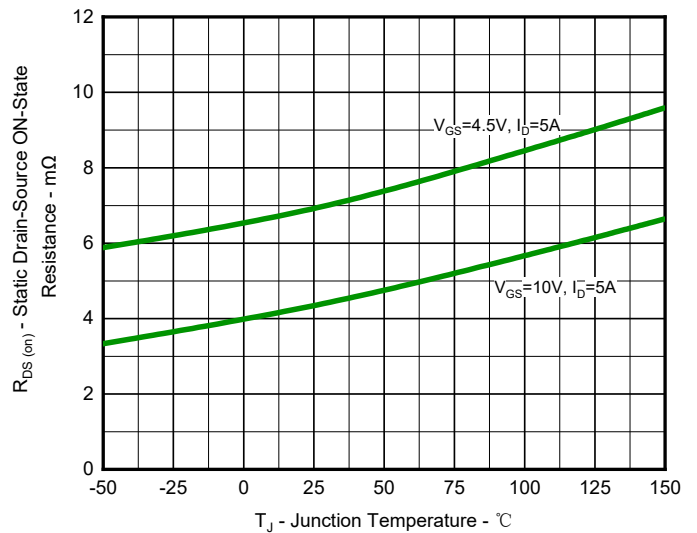
**Fig.1 Output Characteristics**



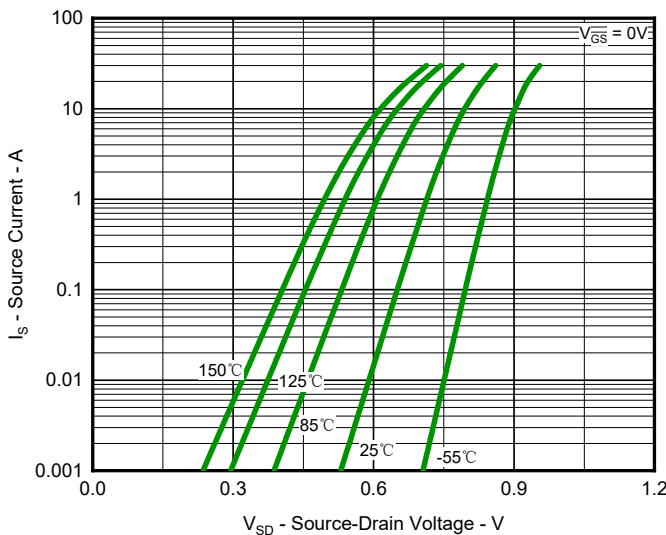
**Fig.2 Typical Transfer Characteristic**



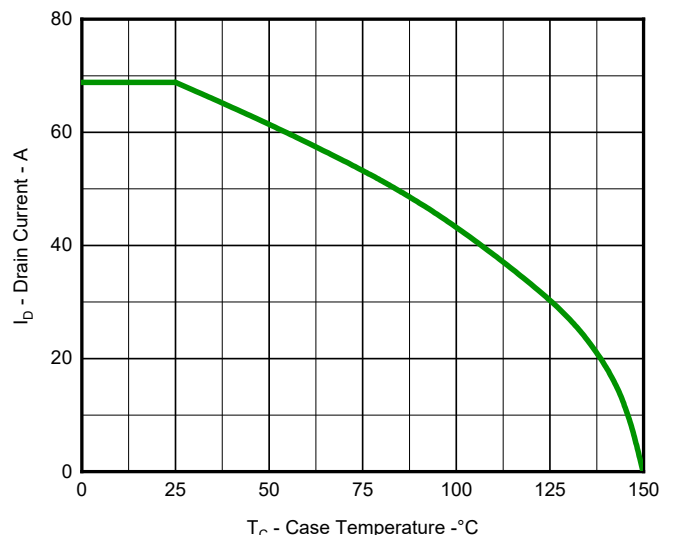
**Fig.3 Typical On-Resistance vs Drain Current and Temperature**



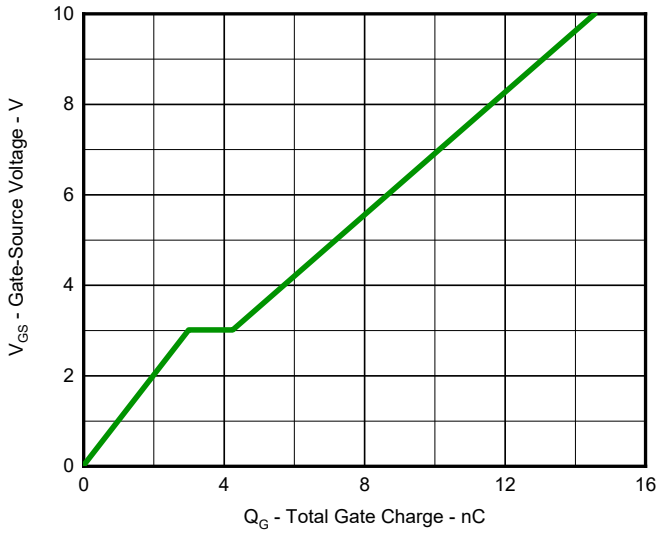
**Fig.4 On-Resistance Variation with Temperature**



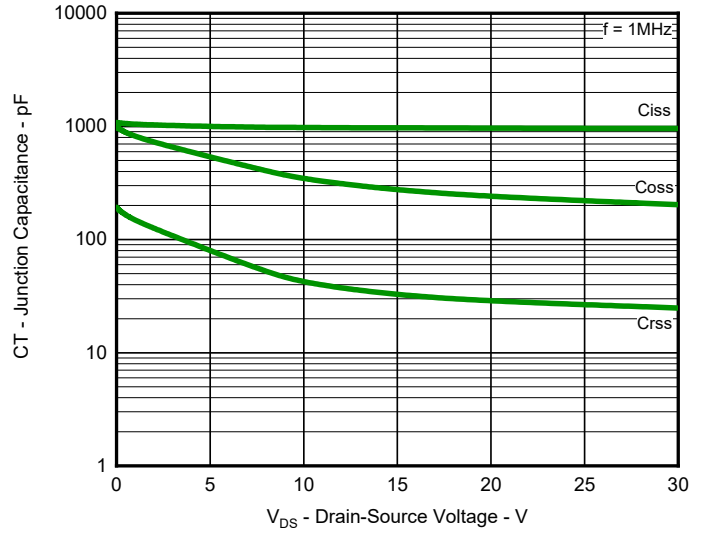
**Fig.5 Diode Forward Voltage vs. Current**



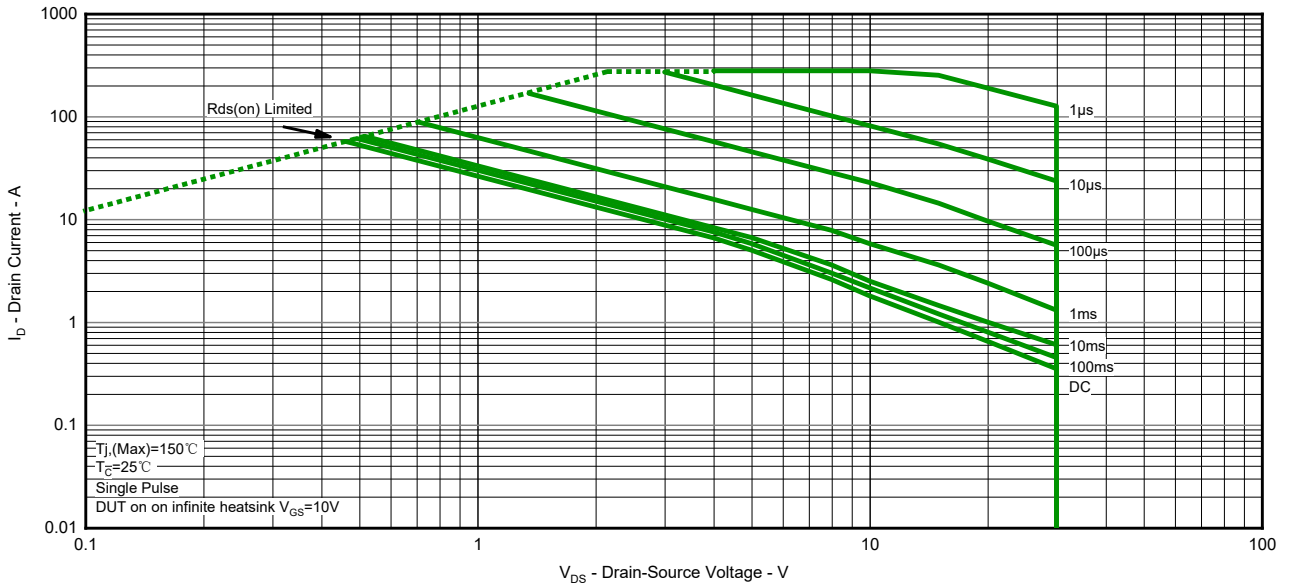
**Fig.6 Maximum Drain Current vs. Case Temperature**



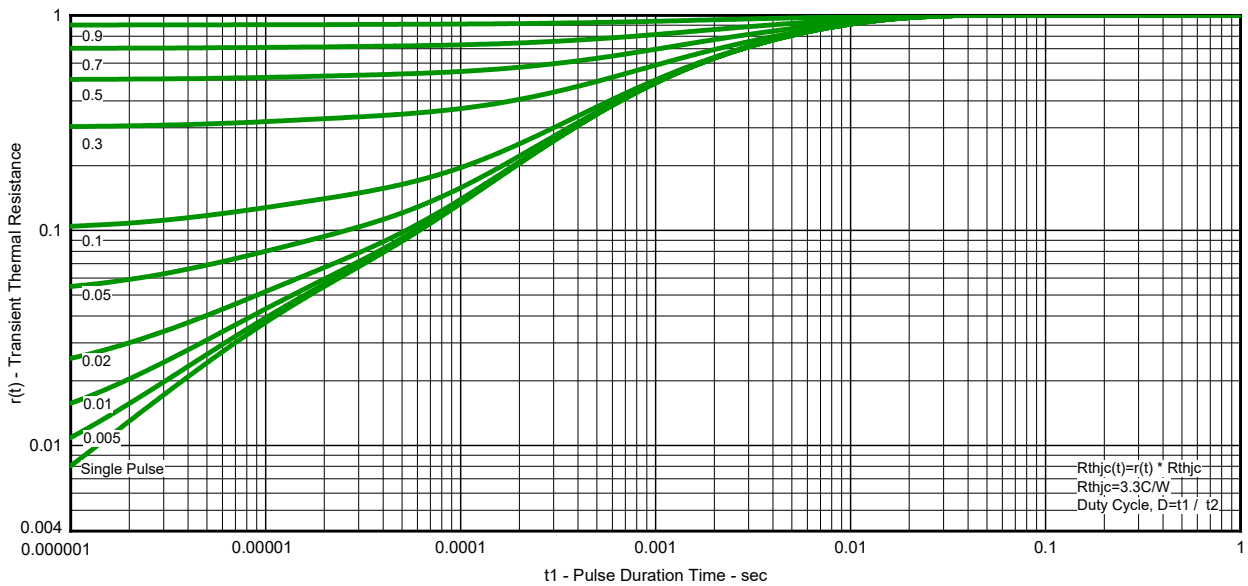
**Fig.7 Gate Charge Characteristics**



**Fig.8 Typical Junction Capacitance**

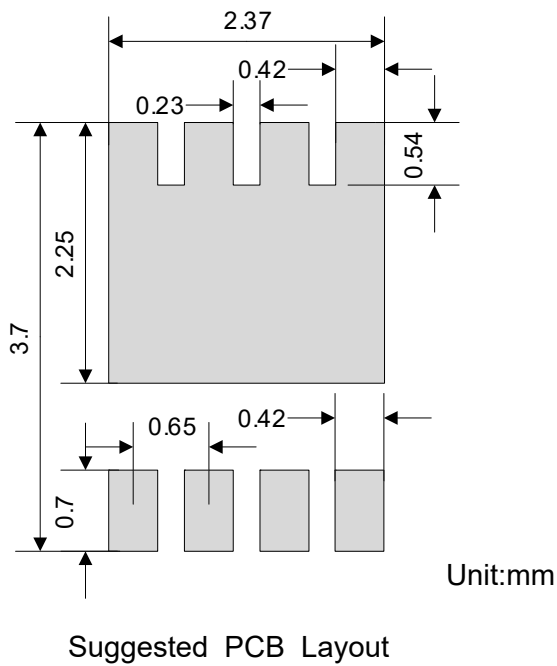
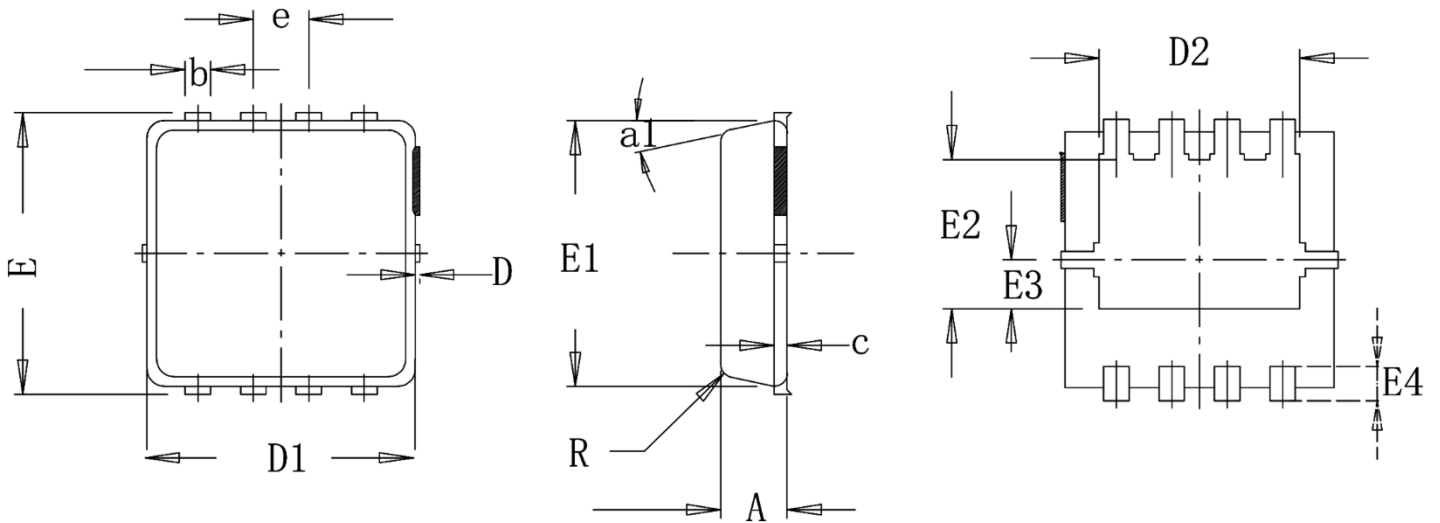


**Fig.9 Safe Operation Area**



**Fig.10 Transient Thermal Resistance**

## Product Dimension (DFN3333-8L)



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.75	0.81	0.030	0.032
b	0.297	0.35	0.012	0.014
c	0.152 Ref.		0.006 Ref.	
D	0.00	0.10	0.000	0.004
D1	3.12	3.18	0.123	0.125
D2	2.35 Ref.		0.093 Ref.	
E	3.20	3.40	0.126	0.134
E1	3.09	3.15	0.122	0.124
E2	1.75 Ref.		0.069 Ref.	
E3	0.575 Ref.		0.023 Ref.	
E4	0.40 Ref.		0.016 Ref.	
e	0.65 BSC		0.026 BSC	
R	0.15 Ref.		0.006 Ref.	
a1	12°		12°	

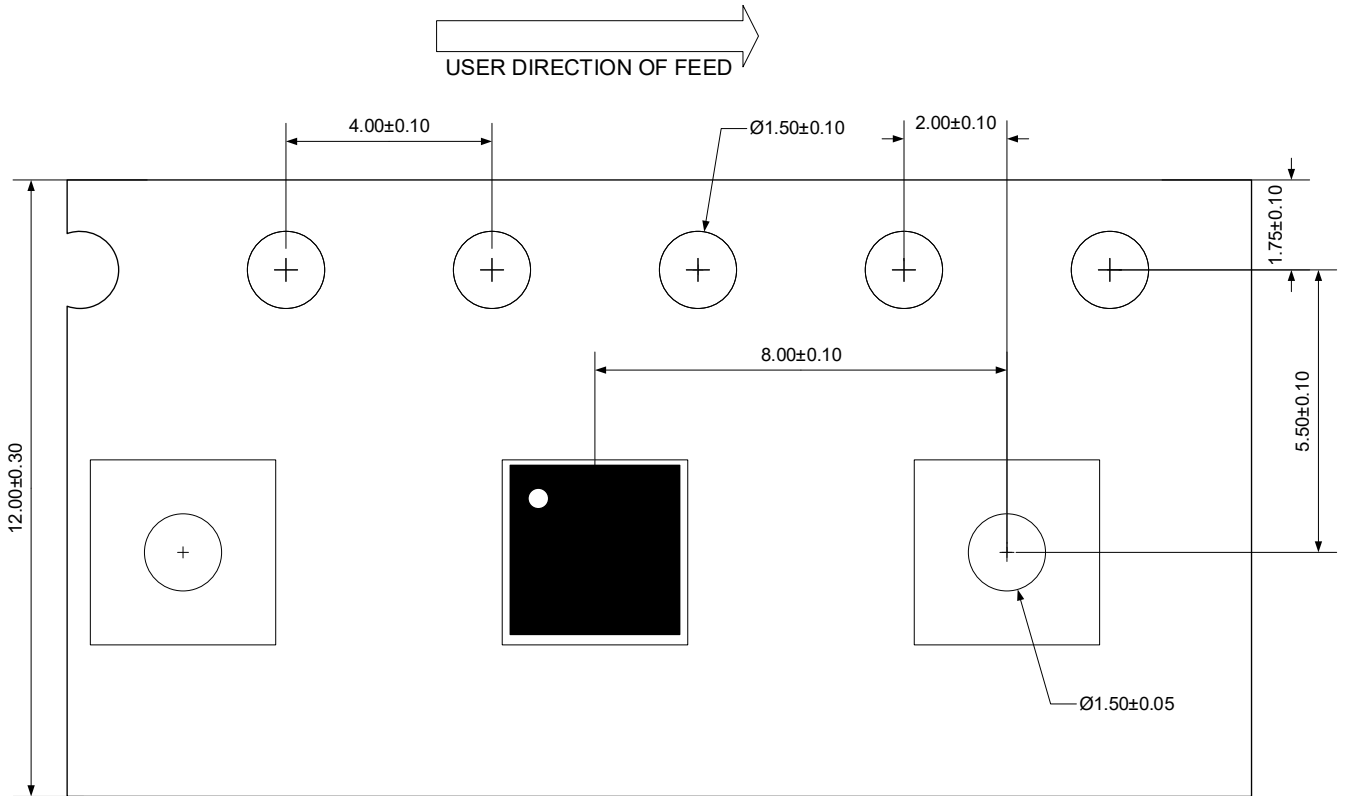
# N-Channel MOSFET

# PSM8PN03R4

## Ordering Information


Device	Package	Reel	Shipping
PSM8PN03R4	DFN3333-8L	13"	5000 / Tape & Reel

## Load With Information



Unit:mm


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